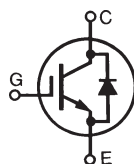


# HiPerFAST™ IGBTs C2-Class High Speed w/ Diode

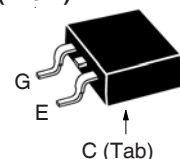
**IXGA16N60C2D1**  
**IXGP16N60C2D1**  
**IXGH16N60C2D1**

**V<sub>CES</sub> = 600V**  
**I<sub>C110</sub> = 16A**  
**V<sub>CE(sat)</sub> ≤ 3.0V**  
**t<sub>fi(typ)</sub> = 33ns**

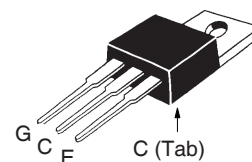


Symbol	Test Conditions	Maximum Ratings	
V <sub>CES</sub>	T <sub>J</sub> = 25°C to 150°C	600	V
V <sub>CGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GE</sub> = 1MΩ	600	V
V <sub>GES</sub>	Continuous	±20	V
V <sub>GEM</sub>	Transient	±30	V
I <sub>C25</sub>	T <sub>C</sub> = 25°C	40	A
I <sub>C110</sub>	T <sub>C</sub> = 110°C	16	A
I <sub>F110</sub>	T <sub>C</sub> = 110°C	11	A
I <sub>CM</sub>	T <sub>C</sub> = 25°C, 1ms	100	A
<b>SSOA</b> <b>(RBSOA)</b>	V <sub>GE</sub> = 15V, T <sub>J</sub> = 125°C, R <sub>G</sub> = 22Ω Clamped Inductive load	I <sub>CM</sub> = 32 V <sub>CE</sub> ≤ V <sub>CES</sub>	A
P <sub>C</sub>	T <sub>C</sub> = 25°C	150	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
M <sub>d</sub>	Mounting Torque (TO-220 & TO-247)	1.13/10	Nm/lb.in.
F <sub>C</sub>	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
T <sub>L</sub>	Maximum Lead Temperature for Soldering	300	°C
T <sub>SOLD</sub>	1.6mm (0.062 in.) from Case for 10s	260	°C
<b>Weight</b>	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

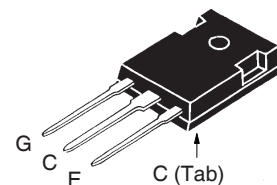
TO-263 AA (IXGA)



TO-220AB (IXGP)



TO-247 (IXGH)



G = Gate      C = Collector  
E = Emitter    Tab = Collector

## Features

- Optimized for Low Switching Losses
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- International Standard Packages

## Advantages

- High Power Density
- Low Gate Drive Requirement

## Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions (T <sub>J</sub> = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V <sub>GE(th)</sub>	I <sub>C</sub> = 250μA, V <sub>CE</sub> = V <sub>GE</sub>	3.0		5.5 V
I <sub>CES</sub>	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V T <sub>J</sub> = 125°C			25 μA 1 mA
I <sub>GES</sub>	V <sub>CE</sub> = 0V, V <sub>GE</sub> = ±20V			±100 nA
V <sub>CE(sat)</sub>	I <sub>C</sub> = 12A, V <sub>GE</sub> = 15V, Note1 T <sub>J</sub> = 125°C		1.8	3.0 V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 12\text{A}, V_{CE} = 10\text{V}$ , Note 1	8		S
$C_{ies}$ $C_{oes}$ $C_{res}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		657	pF
			72	pF
			22	pF
$Q_{g(on)}$ $Q_{ge}$ $Q_{gc}$	$I_C = 12\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		25	nC
			5	nC
			13	nC
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 12\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 22\Omega$ Note 2		16	ns
			17	ns
			0.16	mJ
			75	ns
			33	ns
			0.09	0.16 mJ
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 12\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 22\Omega$ Note 2		16	ns
			18	ns
			0.27	mJ
			115	ns
			100	ns
			0.27	mJ
$R_{thJC}$ $R_{thCK}$	TO-220 TO-247		0.83	$^\circ\text{C/W}$
		0.50	$^\circ\text{C/W}$	
		0.21	$^\circ\text{C/W}$	

**Reverse Diode (FRED)**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 10\text{A}, V_{GE} = 0\text{V}$ , Note 1 $T_J = 125^\circ\text{C}$		1.7	3.0 V V
$I_{RM}$ $t_{rr}$ $t_{rr}$	$I_F = 12\text{A}, V_{GE} = 0\text{V}$ , $-di_F/dt = 100\text{A}/\mu\text{s}, V_R = 100\text{V}, T_J = 125^\circ\text{C}$		2.5	A
		$I_F = 1\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}, V_R = 30\text{V}$		110
			30	ns
$R_{thJC}$				2.5 $^\circ\text{C/W}$

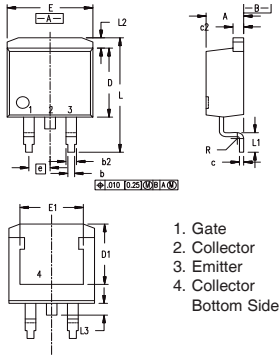
**Notes:**

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}(\text{Clamp})$ ,  $T_J$  or  $R_G$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

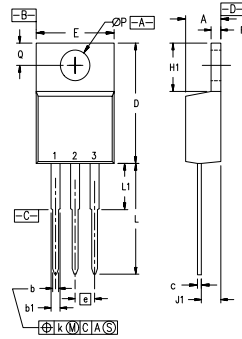
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

### TO-263 (IXGA) Outline



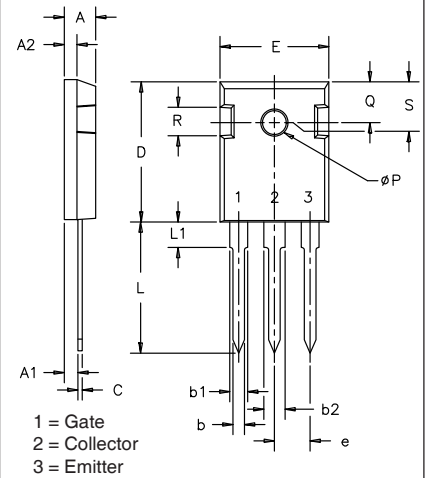
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.40	0.74	.016	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.280	.320
E	9.65	10.41	.380	.405
E1	6.22	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.13	0	.005

### TO-220 (IXGP) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

### TO-247 (IXGH) AD Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A1	.087	.102	2.2	2.54
A2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b1	.065	.084	1.65	2.13
b2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
ØP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

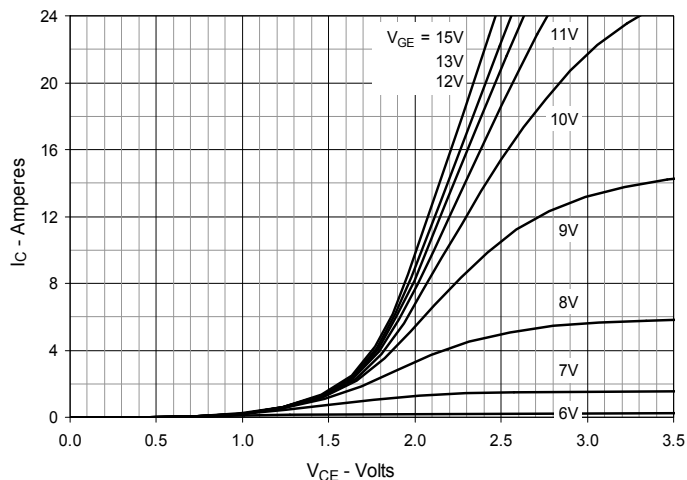


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

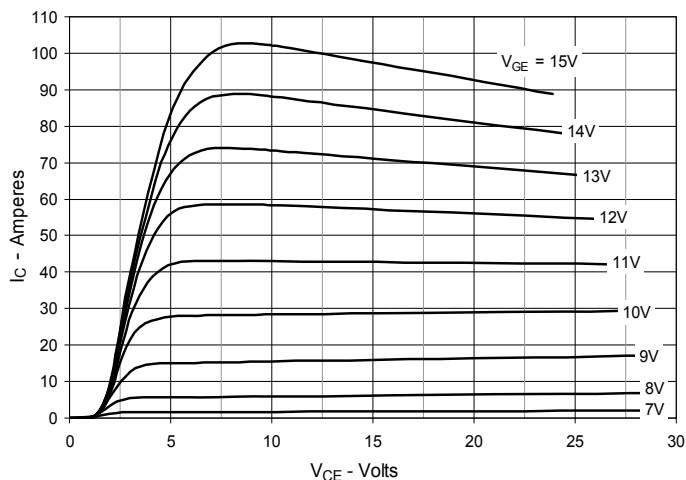


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

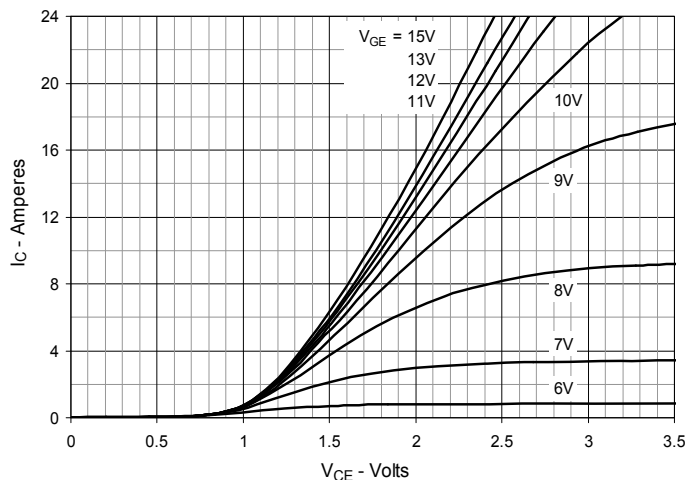


Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature

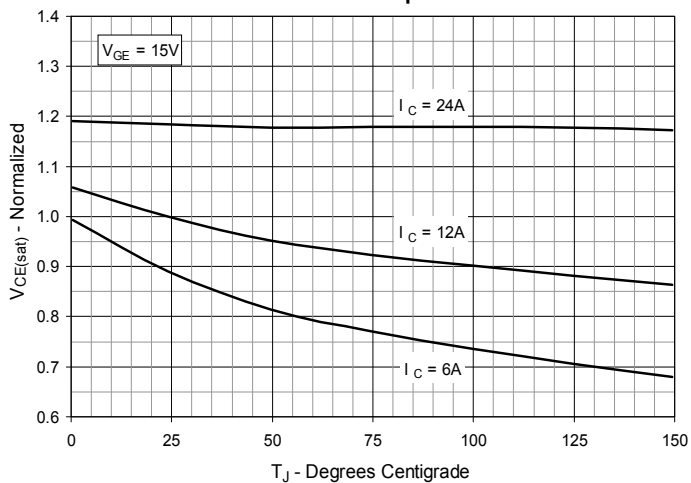


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

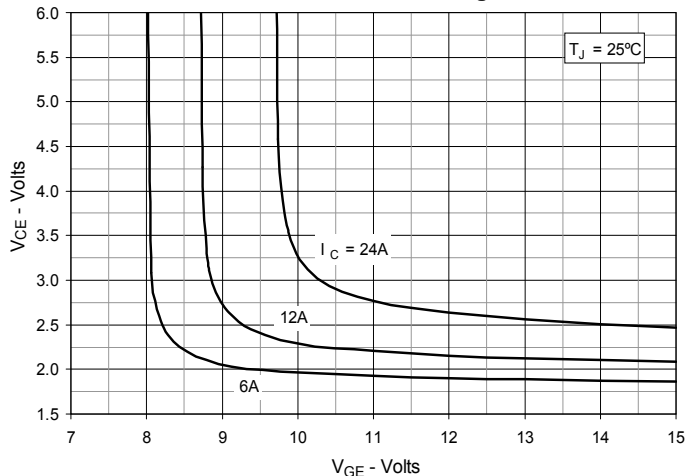
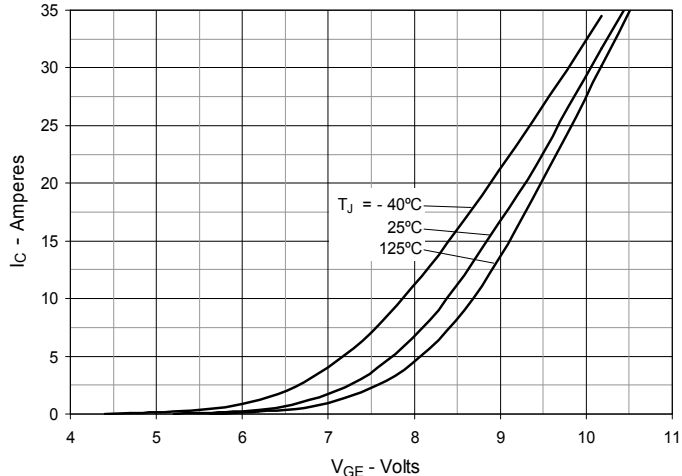
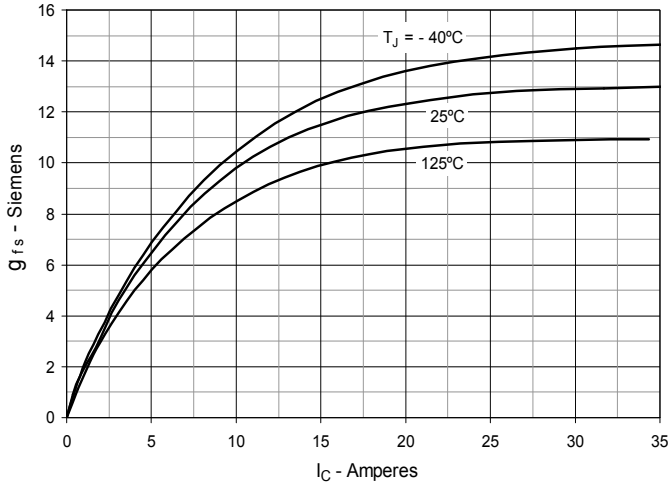


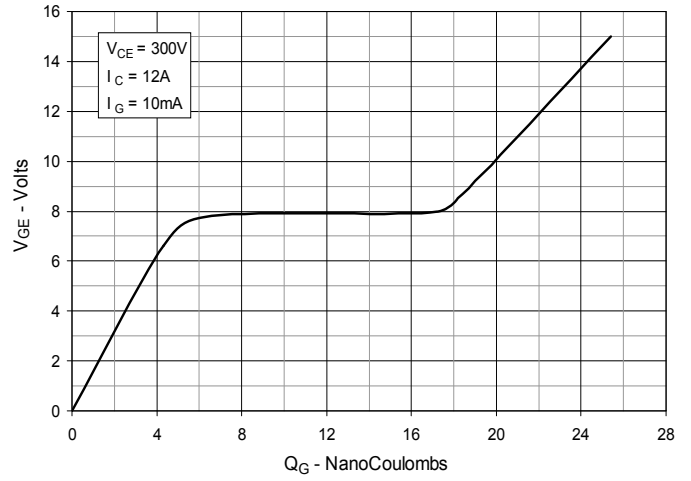
Fig. 6. Input Admittance



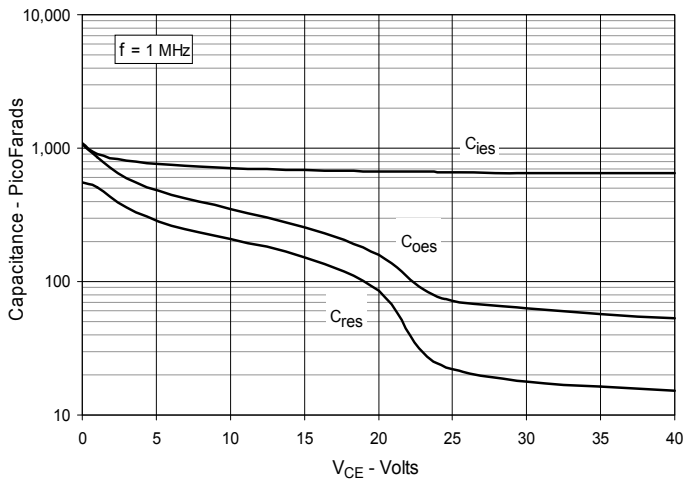
**Fig. 7. Transconductance**



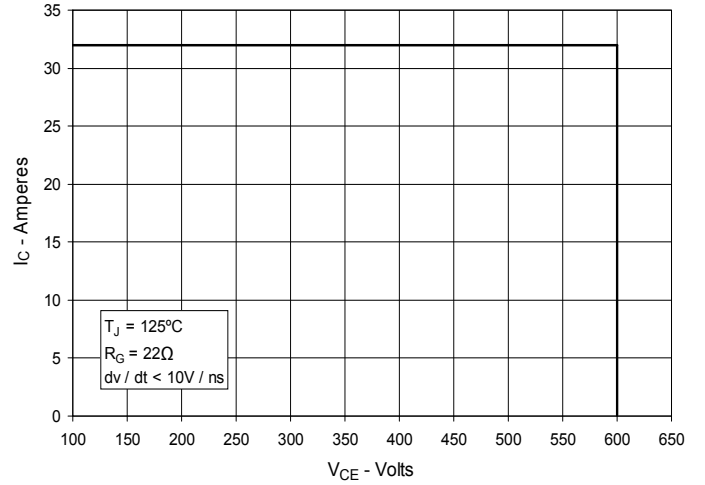
**Fig. 8. Gate Charge**



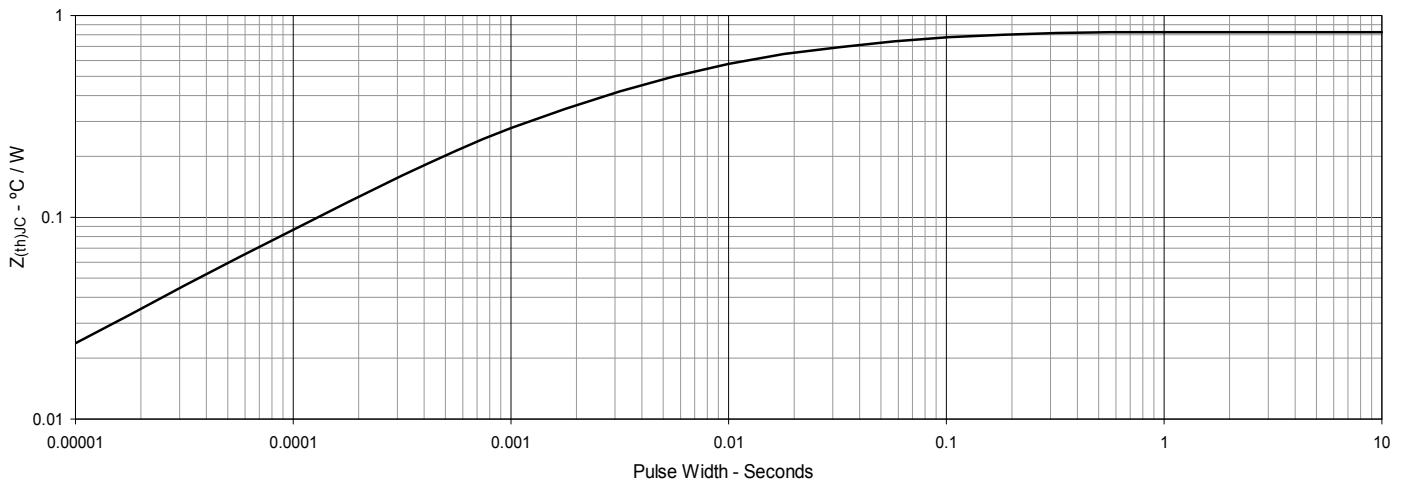
**Fig. 9. Capacitance**



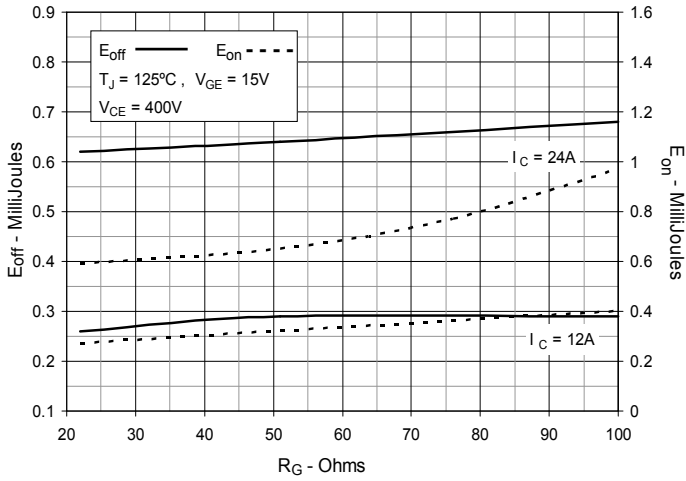
**Fig. 10. Reverse-Bias Safe Operating Area**



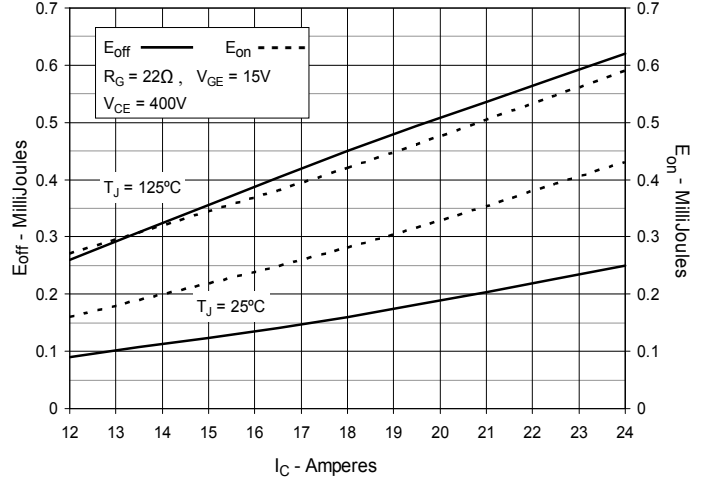
**Fig. 11. Maximum Transient Thermal Impedance**



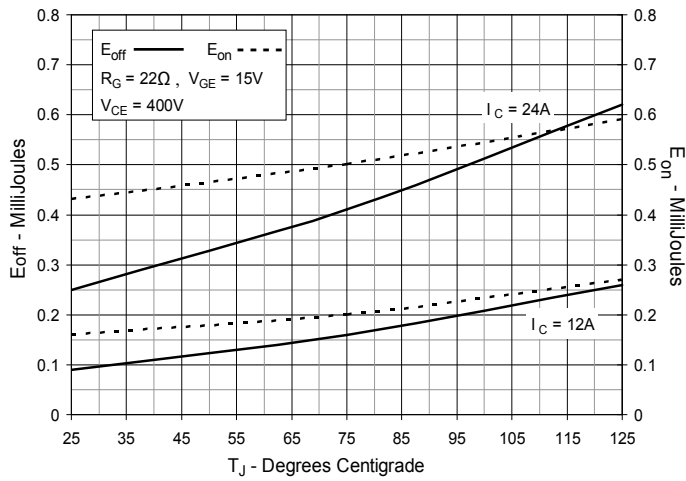
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



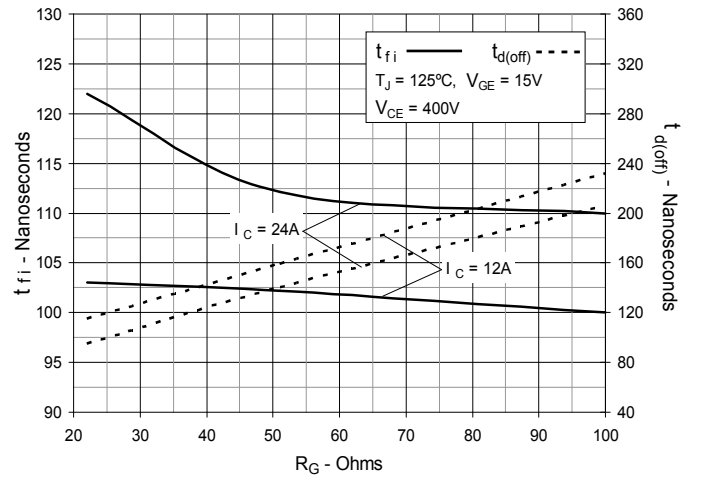
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



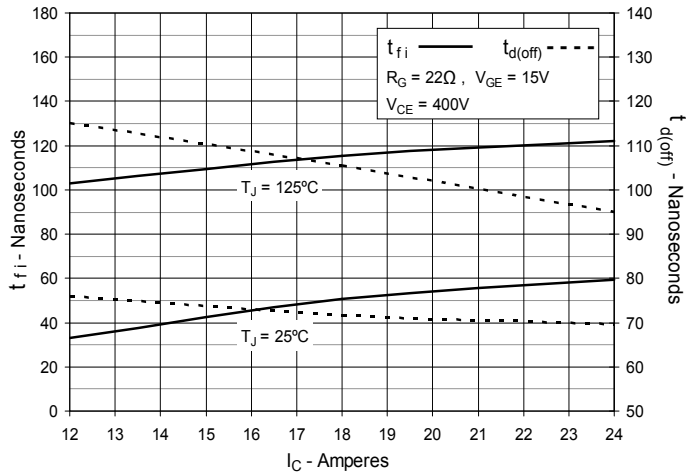
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



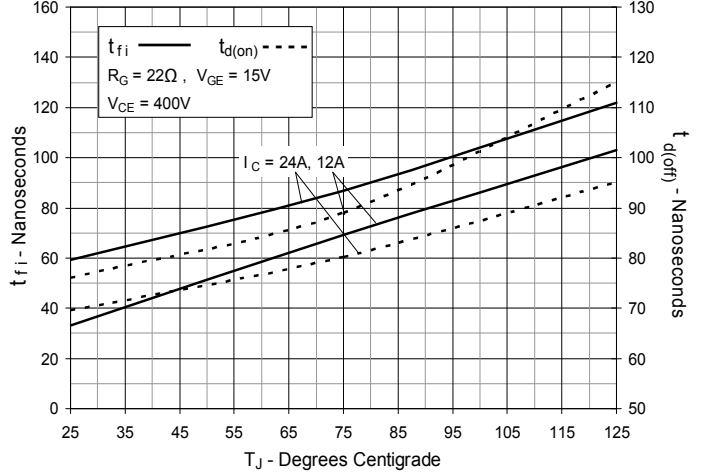
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



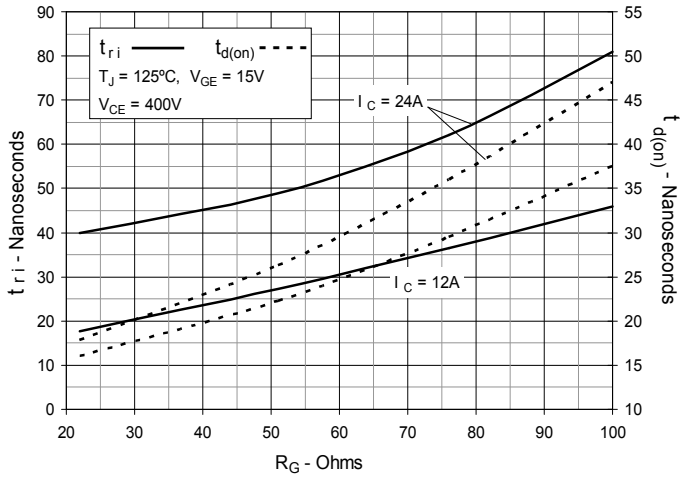
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



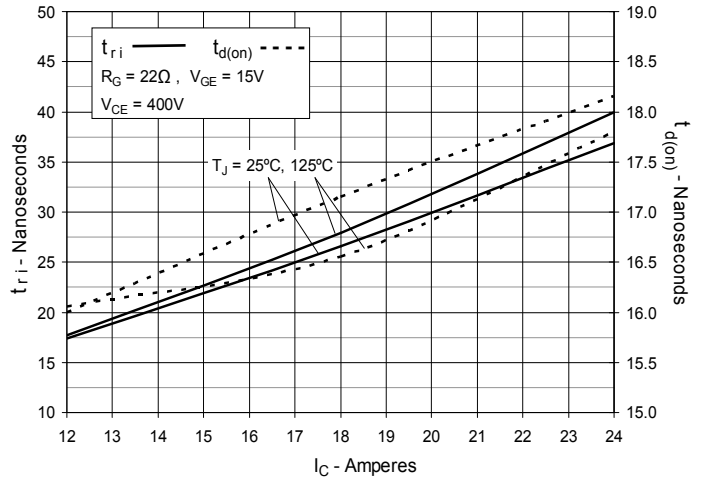
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**

